[Title]

Annealed Wafer and Manufacturing Method of Annealed wafer

[ABSTRACT]

[PROBLEM]

An annealed wafer in which oxygen precipitation is uniform in the substrate plane and a manufacturing method thereof are provided.

[MEANS FOR SOLVING THE PROBLEM]

A nitrogen-doped silicon single crystal substrate pulled at the cooling rate of 1100 to 1000°C which is 4°C/minute or more during crystal growth, wherein the nitrogen concentration is 1×10^{14} to 5×10^{15} atoms/cm^3 and V/G satisfies predetermined conditions as crystal growth conditions at silicon single crystal manufacturing serves as a substrate, and the substrate is subjected to heat treatment in a non-oxidative atmosphere.

[SELECTED FIGURE] Fig. 3